Paul Fons

List of Publications by Year in Descending Order

323 papers	9,338 citations	49 h-index	85 g-index
347 ext. papers	10,032 ext. citations	3.5 avg, IF	5.82 L-index

#	Paper	IF	Citations
323	The formation of a one-dimensional van der Waals selenium crystal from the three-dimensional amorphous phase: A spectroscopic signature of van der Waals bonding. *Applied Physics Letters*, **2022**, 120, 033103	3.4	1
322	Dimensional transformation of chemical bonding during crystallization in a layered chalcogenide material. *Scientific Reports*, **2021**, 11, 4782	4.9	6
321	Dielectric relaxation in amorphous and crystalline Sb2Te3 thin films. *Journal of Materials Science: Materials in Electronics*, **2021**, 32, 14072-14078	2.1	3
320	Role of the Cu-Deficient Interface in Cu(In,Ga)Se2 Thin-Film Photovoltaics with Alkali-Metal Doping. *Physical Review Applied*, **2021**, 15,	4.3	1
319	Electric Fields and Interfacial Phase-Change Memory Structures. *Physica Status Solidi - Rapid Research Letters*, **2021**, 15, 2000412	2.5	1
318	Chalcogenide Materials Engineering for Phase-Change Memory and Future Electronics Applications: From Sb□□e to Bi□□e. *Physica Status Solidi - Rapid Research Letters*, **2021**, 15, 2000414	2.5	3
317	Phase Change Materials for Optical Disc and Display Applications **2021**, 681-711		
316	Ultrafast scattering dynamics of coherent phonons in Bi1□ Sb x in the Weyl semimetal phase. *New Journal of Physics*, **2021**, 23, 023034	2.9	1
315	Understanding the low resistivity of the amorphous phase of Cr2Ge2Te6 phase-change material: Experimental evidence for the key role of Cr clusters. *Physical Review Materials*, **2021**, 5,	3.2	1
314	Evolution of the local structure surrounding nitrogen atoms upon the amorphous to crystalline phase transition in nitrogen-doped Cr2Ge2Te6 phase-change material. *Applied Surface Science*, **2021**, 556, 149760	6.7	0
313	Crystallization of Ge2Sb2Te5 under high hydrostatic pressures: Differences in nanoscale atomic ordering in as-deposited and pressure-induced amorphous phases. *Journal of Alloys and Compounds* , **2021**, 874, 159980	5.7	0
312	Polymorphism of CdTe in the Few-Monolayer Limit. *Physica Status Solidi - Rapid Research Letters*, **2021**, 15, 2100358	2.5	0
311	Amorphous-to-Crystal Transition in Quasi-Two-Dimensional MoS2: Implications for 2D Electronic Devices. *ACS Applied Nano Materials*, **2021**, 4, 8834-8844	5.6	4
310	Recent developments concerning the sputter growth of chalcogenide-based layered phase-change materials. *Materials Science in Semiconductor Processing*, **2021**, 135, 106079	4.3	3
309	Phase-Change Alloys: Structural Aspects **2021**, 323-339		
308	Crystalline Sb2Te3: Side Surfaces and Disappearance of Dirac Cones. *Physica Status Solidi - Rapid Research Letters*, **2021**, 15, 2000418	2.5	2
307	The importance of contacts in Cu2GeTe3 phase change memory devices. *Journal of Applied Physics*, **2020**, 128, 165105	2.5	5

306	Effects of electric and magnetic fields on the resistive switching operation of iPCM. *Applied Physics Letters*, **2020**, 116, 201903	3.4	1
305	Lithium-Doping Effects in Cu(In,Ga)Se Thin-Film and Photovoltaic Properties. *ACS Applied Materials & Interfaces*, **2020**, 12, 25058-25065	9.5	10
304	Polarization Processes in Thin Layers of Amorphous MoS2 Obtained by RF Magnetron Sputtering. *Semiconductors*, **2020**, 54, 558-562	0.7	
303	Structural Metastability in Chalcogenide Semiconductors: The Role of Chemical Bonding. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 2000138	1.3	2
302	Structural and Dielectric Study of Thin Amorphous Layers of the GeSbTe System Prepared by RF Magnetron Sputtering. *Semiconductors*, **2020**, 54, 201-204	0.7	
301	Ultrafast dynamics of the low frequency shear phonon in 1T?- MoTe 2. *Applied Physics Letters*, **2020**, 116, 093103	3.4	6
300	High-quality sputter-grown layered chalcogenide films for phase change memory applications and beyond. *Journal Physics D: Applied Physics*, **2020**, 53, 284002	3	15
299	Dielectric relaxation in the GeSb2Te4 phase-change material **2020**,		1
298	Polycrystalline CuGaSe2 thin film growth and photovoltaic devices fabricated on alkali-free and alkali-containing substrates. *Journal of Crystal Growth*, **2020**, 532, 125407	1.6	3
297	Dielectric Relaxation and Charge Transfer in Amorphous MoS2 Thin Films. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 2000114	1.3	4
296	Soft X-ray Absorption Spectroscopy Probes OHInteractions in Epoxy-Based Polymers. *Journal of Physical Chemistry C*, **2020**, 124, 9622-9627	3.8	6
295	Terahertz spectroscopic characterization of Ge2Sb2Te5 phase change materials for photonics applications. *Journal of Materials Chemistry C*, **2019**, 7, 8209-8215	7.1	12
294	Transient Fano Resonance in topological insulators observed by coherent phonon spectroscopy. *EPJ Web of Conferences*, **2019**, 205, 04021	0.3	
293	High-Speed Bipolar Switching of Sputtered GeTe/SbTe Superlattice iPCM with Enhanced Cyclability. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1900105	2.5	12
292	Systematic materials design for phase-change memory with small density changes for high-endurance non-volatile memory applications. *Applied Physics Express*, **2019**, 12, 051008	2.4	5
291	Chalcogenide van der Waals superlattices: a case example of interfacial phase-change memory. *Pure and Applied Chemistry*, **2019**, 91, 1777-1786	2.1	4
290	Origin of resistivity contrast in interfacial phase-change memory: The crucial role of Ge/Sb intermixing. *Applied Physics Letters*, **2019**, 114, 132102	3.4	27
289	Investigation of the oxidation process in GeTe-based phase change alloy using Ge K-edge XANES spectroscopy. *Pure and Applied Chemistry*, **2019**, 91, 1769-1775	2.1	1

288	Photon energy dependence of Kerr rotation in GeTe/SbTe chalcogenide superlattices. *Journal of Physics Condensed Matter*, **2019**, 31, 415502	1.8	1
287	Similarities and Critical Differences in Heavy Alkali-Metal Rubidium and Cesium Effects on Chalcopyrite Cu(In,Ga)Se2 Thin-Film Solar Cells. *Journal of Physical Chemistry C*, **2019**, 123, 17757-17764	3.8	28
286	Cr-Triggered Local Structural Change in CrGeTe Phase Change Material. *ACS Applied Materials & Interfaces*, **2019**, 11, 43320-43329	9.5	13
285	Terahertz generation measurements of multilayered GeTe-SbTe phase change materials. *Optics Letters*, **2019**, 44, 1355-1358	3	6
284	Resistive switching characteristics of interfacial phase-change memory at elevated temperature. *Japanese Journal of Applied Physics*, **2018**, 57, 04FE06	1.4	6
283	Coherent Dirac plasmons in topological insulators. *Physical Review B*, **2018**, 97,	3.3	7
282	Si-Doped Cu(In,Ga)Se2 Photovoltaic Devices with Energy Conversion Efficiencies Exceeding 16.5% without a Buffer Layer. *Advanced Energy Materials*, **2018**, 8, 1702391	21.8	7
281	Understanding the fast phase-change mechanism of tetrahedrally bonded Cu2GeTe3: Comprehensive analyses of electronic structure and transport phenomena. *Physical Review B*, **2018**, 97,	3.3	9
280	A cascading nonlinear magneto-optical effect in topological insulators. *Scientific Reports*, **2018**, 8, 3908	4.9	7
279	Topological Phase Buried in a Chalcogenide Superlattice Monitored by Helicity-Dependent Kerr Measurement. *ACS Applied Materials & Interfaces*, **2018**, 10, 26781-26786	9.5	3
278	Effects of RbF postdeposition treatment and heat-light soaking on the metastable acceptor activation of CuInSe2 thin film photovoltaic devices. *Applied Physics Letters*, **2018**, 113, 063901	3.4	19
277	(Invited) Sputter Growth of Chalcogenide Superlattice Films for Future Phase Change Memory Applications. *ECS Transactions*, **2018**, 86, 49-54	1	4
276	Zener Tunneling Breakdown in Phase-Change Materials Revealed by Intense Terahertz Pulses. *Physical Review Letters*, **2018**, 121, 165702	7.4	13
275	Reconfiguration of van der Waals Gaps as the Key to Switching in GeTe/Sb2Te3 Superlattices. *MRS Advances*, **2018**, 3, 3413-3418	0.7	0
274	All-Optical Detection of Periodic Structure of Chalcogenide Superlattice Using Coherent Folded Acoustic Phonons. *Physica Status Solidi - Rapid Research Letters*, **2018**, 12, 1800246	2.5	
273	Detection of N-Te bonds in the as-deposited amorphous nitrogen-doped GeTe-based phase change alloys using N K-edge XANES spectroscopy and their impact on crystallization. *Journal of Alloys and Compounds*, **2017**, 704, 254-259	5.7	5
272	Atomic Reconfiguration of van der Waals Gaps as the Key to Switching in GeTe/SbTe Superlattices. *ACS Omega*, **2017**, 2, 6223-6232	3.9	48
271	Enhancement of coherent phonon amplitude in phase-change materials by near-infrared laser irradiation. *Applied Physics Letters*, **2017**, 111, 112101	3.4	3

270	Compositional tuning in sputter-grown highly-oriented Bi-Te films and their optical and electronic structures. *Nanoscale*, **2017**, 9, 15115-15121	7.7	14
269	Si-Doping Effects in Cu(In,Ga)Se Thin Films and Applications for Simplified Structure High-Efficiency Solar Cells. *ACS Applied Materials & Interfaces*, **2017**, 9, 31119-31128	9.5	11
268	A Magnetoresistance Induced by a Nonzero Berry Phase in GeTe/Sb2Te3 Chalcogenide Superlattices. *Advanced Functional Materials*, **2017**, 27, 1702243	15.6	22
267	Electronic Structure of Transition-Metal Based Cu2GeTe3 Phase Change Material: Revealing the Key Role of Cu d Electrons. *Chemistry of Materials*, **2017**, 29, 7440-7449	9.6	18
266	Local structure of the crystalline and amorphous states of Ga2Te3 phase-change alloy without resonant bonding: A combined x-ray absorption and ab initio study. *Physical Review B*, **2017**, 95,	3.3	12
265	Pressure-Induced Phase Transitions in GeTe-Rich Ge-Sb-Te Alloys across the Rhombohedral-to-Cubic Transitions. *Inorganic Chemistry*, **2017**, 56, 7687-7693	5.1	3
264	Manipulating the Bulk Band Structure of Artificially Constructed van der Waals Chalcogenide Heterostructures. *ACS Applied Materials & Interfaces*, **2017**, 9, 23918-23925	9.5	15
263	A comparative study of the effects of sputtering deposition conditions for ZnO surface electrode layers on Cu(In,Ga)Se2 and CuGaSe2 solar cells. *Thin Solid Films*, **2017**, 633, 49-54	2.2	5
262	Strain engineering of atomic and electronic structures of few-monolayer-thick GaN. *Physical Review Materials*, **2017**, 1,	3.2	15
261	Phase-Change Memory Materials. *Springer Handbooks*, **2017**, 1-1	1.3	3
260	Insights into the physics and chemistry of chalcogenides obtained from x-ray absorption spectroscopy. *Semiconductor Science and Technology*, **2017**, 32, 123003	1.8	6
259	Anisotropic lattice response induced by a linearly-polarized femtosecond optical pulse excitation in interfacial phase change memory material. *Scientific Reports*, **2016**, 6, 19758	4.9	7
258	Sub-nanometre resolution of atomic motion during electronic excitation in phase-change materials. *Scientific Reports*, **2016**, 6, 20633	4.9	22
257	Instability and Spontaneous Reconstruction of Few-Monolayer Thick GaN Graphitic Structures. *Nano Letters*, **2016**, 16, 4849-56	11.5	39
256	Interface oxygen and heat sensitivity of Cu(In,Ga)Se2 and CuGaSe2 solar cells. *Applied Physics Letters*, **2016**, 108, 203902	3.4	9
255	A two-step process for growth of highly oriented Sb2Te3 using sputtering. *AIP Advances*, **2016**, 6, 045220	1.5	37
254	Electronic excitation-induced semiconductor-to-metal transition in monolayer MoTe2. *Physical Review B*, **2016**, 94,	3.3	37
253	Enhanced Sb2S3 crystallisation by electric field induced silver doping. *Thin Solid Films*, **2016**, 616, 80-85	2.2	11

252	Giant multiferroic effects in topological GeTe-SbTe superlattices. *Science and Technology of Advanced Materials*, **2015**, 16, 014402	7.1	65
251	Laser-driven switching dynamics in phase change materials investigated by time-resolved X-ray absorption spectroscopy. *Phase Transitions*, **2015**, 88, 82-89	1.3	3
250	Femtosecond structural transformation of phase-change materials far from equilibrium monitored by coherent phonons. *Nature Communications*, **2015**, 6, 8367	17.4	46
249	Local structure of epitaxial GeTe and Ge2Sb2Te5 films grown on InAs and Si substrates with (100) and (111) orientations: An x-ray absorption near-edge structure study. *Journal of Applied Physics*, **2015**, 117, 125308	2.5	7
248	Self-organized van der Waals epitaxy of layered chalcogenide structures. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 2151-2158	1.3	54
247	Understanding Phase-Change Memory Alloys from a Chemical Perspective. *Scientific Reports*, **2015**, 5, 13698	4.9	41
246	Anomalous Phase Change in [(GeTe)2/(Sb2Te3)]20 Superlattice Observed by Coherent Phonon Spectroscopy. *Springer Proceedings in Physics*, **2015**, 199-201	0.2	2
245	Coherent gigahertz phonons in GeSbTe phase-change materials. *Journal of Physics Condensed Matter*, **2015**, 27, 485402	1.8	0
244	Ultrafast Lattice Dynamics of Phase-Change Materials Monitored by a Pump-Pump-Probe Technique. *Springer Proceedings in Physics*, **2015**, 210-213	0.2	
243	Mirror-symmetric magneto-optical Kerr rotation using visible light in [(GeTe)2(Sb2Te3)1]n topological superlattices. *Scientific Reports*, **2014**, 4, 5727	4.9	51
242	Structural tuning of wide-gap chalcopyrite CuGaSe2 thin films and highly efficient solar cells: differences from narrow-gap Cu(In,Ga)Se2. *Progress in Photovoltaics: Research and Applications*, **2014**, 22, 821-829	6.8	54
241	Doping of ZnO nanowires using phosphorus diffusion from a spin-on doped glass source. *Journal of Applied Physics*, **2014**, 115, 194302	2.5	1
240	Buried p-n junction formation in CuGaSe2 thin-film solar cells. *Applied Physics Letters*, **2014**, 104, 031606	3.4	26
239	Study of band inversion in the PbxSn1-xTe class of topological crystalline insulators using x-ray absorption spectroscopy. *Journal of Physics Condensed Matter*, **2014**, 26, 475502	1.8	8
238	Ferroelectric switching in epitaxial GeTe films. *APL Materials*, **2014**, 2, 066101	5.7	53
237	Excitation-Assisted Disordering of GeTe and Related Solids with Resonant Bonding. *Journal of Physical Chemistry C*, **2014**, 118, 10248-10253	3.8	25
236	Local structure of the SnTe topological crystalline insulator: Rhombohedral distortions emerging from the rocksalt phase. *Physical Review B*, **2014**, 90,	3.3	19
235	Interfacial alkali diffusion control in chalcopyrite thin-film solar cells. *ACS Applied Materials & Interfaces*, **2014**, 6, 14123-30	9.5	21

234	Coherent phonon study of (GeTe)l(Sb2Te3)m interfacial phase change memory materials. *Applied Physics Letters*, **2014**, 105, 151902	3.4	14
233	Hard x-ray photoelectron spectroscopy study of Ge2Sb2Te5; as-deposited amorphous, crystalline, and laser-reamorphized. *Applied Physics Letters*, **2014**, 104, 061909	3.4	6
232	Ge L3-edge x-ray absorption near-edge structure study of structural changes accompanying conductivity drift in the amorphous phase of Ge2Sb2Te5. *Journal of Applied Physics*, **2014**, 115, 173501	2.5	28
231	Picosecond strain dynamics in Ge2Sb2Te5 monitored by time-resolved x-ray diffraction. *Physical Review B*, **2014**, 90,	3.3	13
230	Ab-initio calculations and structural studies of (SiTe)2(Sb2Te3)n (n: 1, 2, 4 and 6) phase-change superlattice films. *Physica Status Solidi - Rapid Research Letters*, **2014**, 8, 302-306	2.5	27
229	Athermal amorphization of crystallized chalcogenide glasses and phase-change alloys. *Physica Status Solidi (B): Basic Research*, **2014**, 251, 1297-1308	1.3	11
228	Ferroelectric Order Control of the Dirac-Semimetal Phase in GeTe-Sb2Te3 Superlattices. *Advanced Materials Interfaces*, **2014**, 1, 1300027	4.6	133
227	Texture and morphology variations in (In,Ga)2Se3 and Cu(In,Ga)Se2 thin films grown with various Se source conditions. *Progress in Photovoltaics: Research and Applications*, **2013**, 21, 544-553	6.8	31
226	Impact of a binary Ga2Se3 precursor on ternary CuGaSe2 thin-film and solar cell device properties. *Applied Physics Letters*, **2013**, 103, 143903	3.4	18
225	Local instability of p-type bonding makes amorphous GeTe a lone-pair semiconductor. *Physical Review B*, **2013**, 87,	3.3	28
224	Vacancy-mediated three-center four-electron bonds in GeTe-Sb2Te3 phase-change memory alloys. *Physical Review B*, **2013**, 87,	3.3	59
223	Nanometer Resolution XANES Imaging ofin situ switched individual PC-RAM devices. *Materials Research Society Symposia Proceedings*, **2013**, 1563, 1		1
222	Selective detection of tetrahedral units in amorphous GeTe-based phase change alloys using Ge L3-edge x-ray absorption near-edge structure spectroscopy. *Applied Physics Letters*, **2013**, 102, 111904	3.4	28
221	Ultrafast optical manipulation of atomic motion in multilayer Ge-Sb-Te phase change materials. *EPJ Web of Conferences*, **2013**, 41, 03007	0.3	2
220	A hard X-ray nanospectroscopy station at SPring-8 BL39XU. *Journal of Physics: Conference Series*, **2013**, 430, 012017	0.3	21
219	A reconsideration of the thermodynamics of phase-change switching. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 1932-1938	1.3	14
218	Epitaxial phase-change materials. *Physica Status Solidi - Rapid Research Letters*, **2012**, 6, 415-417	2.5	29
217	p-Type conductivity of GeTe: The role of lone-pair electrons. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 1902-1906	1.3	9

216	Disorder in order: A study of local and global order in Ge-rich Ge?Sb?Te alloys. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 1919-1924	1.3	4
215	Crystalline GeTe-based phase-change alloys: Disorder in order. *Physical Review B*, **2012**, 86,	3.3	23
214	Athermal component of amorphisation in phase-change alloys and chalcogenide glasses. *Journal of Non-Crystalline Solids*, **2012**, 358, 2398-2401	3.9	7
213	Amorphous phase of GeTe-based phase-change memory alloys: Polyvalency of Ge?Te bonding and polyamorphism. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 1031-1035	1.6	5
212	Comment on "New structural picture of the Ge2Sb2Te5 phase-change alloy". *Physical Review Letters*, **2012**, 108, 239603; author reply 239602	7.4	6
211	Nanometer Resolution XANES Imaging of Individual PC-RAM Devices. *Materials Research Society Symposia Proceedings*, **2012**, 1431, 26		
210	Polarization dependent optical control of atomic arrangement in multilayer Ge-Sb-Te phase change materials. *Applied Physics Letters*, **2012**, 101, 232101	3.4	15
209	Enhanced crystallization of GeTe from an Sb2Te3 template. *Applied Physics Letters*, **2012**, 100, 021911	3.4	48
208	Local structure of nitrogen in N-doped amorphous and crystalline GeTe. *Applied Physics Letters*, **2012**, 100, 061910	3.4	22
207	Recrystallization of an amorphized epitaxial phase-change alloy: A phoenix arising from the ashes. *Applied Physics Letters*, **2012**, 101, 061903	3.4	18
206	Bond-Selective Excitation and Following Displacement of Ge Atoms in GeTe/Sb2Te3Superlattice. *Acta Physica Polonica A*, **2012**, 121, 336-339	0.6	1
205	Interfacial phase-change memory. *Nature Nanotechnology*, **2011**, 6, 501-5	28.7	528
204	Distortion-triggered loss of long-range order in solids with bonding energy hierarchy. *Nature Chemistry*, **2011**, 3, 311-6	17.6	158
203	CIGS thin films, solar cells, and submodules fabricated using a rf-plasma cracked Se-radical beam source. *Thin Solid Films*, **2011**, 519, 7216-7220	2.2	11
202	The order-disorder transition in GeTe: Views from different length-scales. *Applied Physics Letters*, **2011**, 99, 231907	3.4	55
201	Effect of doping on global and local order in crystalline GeTe. *Applied Physics Letters*, **2011**, 98, 231907	3.4	19
200	Local atomic order of crystalline Ge8Sb2Te11 across the ferroelectric to paraelectric transition: The role of vacancies and static disorder. *Physical Review B*, **2011**, 84,	3.3	16
199	Electrical-field induced giant magnetoresistivity in (non-magnetic) phase change films. *Applied Physics Letters*, **2011**, 99, 152105	3.4	66

198	Intrinsic complexity of the melt-quenched amorphous Ge2Sb2Te5 memory alloy. *Physical Review B*, **2011**, 83,	3.3	100
197	Pressure-induced structural transitions in phase-change materials based on Ge-free Sb-Te alloys. *Physical Review B*, **2011**, 83,	3.3	13
196	Optically Induced Sub-Wavelength Transient Apertures in Sb-Te Based Films. *Materials Research Society Symposia Proceedings*, **2011**, 1338, 32001		1
195	The role of vacancies in the pressure amorphisation phenomenon observed in Ge-Sb-Te phase change alloys. *Materials Research Society Symposia Proceedings*, **2010**, 1251, 10		
194	Stress Limited Scaling of Ge2Sb2Te5. *Materials Research Society Symposia Proceedings*, **2010**, 1251, 2		1
193	Amorphous InSb: Longer bonds yet higher density. *Journal of Applied Physics*, **2010**, 108, 023506	2.5	12
192	Non-melting super-resolution near-field apertures in Sb□Te alloys. *Applied Physics Letters*, **2010**, 97, 161906	3.4	27
191	The first principle computer simulation and real device characteristics of superlattice phase-change memory **2010**,		2
190	Photoassisted amorphization of the phase-change memory alloy Ge2Sb2Te5. *Physical Review B*, **2010**, 82,	3.3	69
189	Toward the ultimate limit of phase change in Ge(2)Sb(2)Te(5). *Nano Letters*, **2010**, 10, 414-9	11.5	201
188	Phase transition in crystalline GeTe: Pitfalls of averaging effects. *Physical Review B*, **2010**, 82,	3.3	83
187	Development of high-efficiency flexible Cu(In,Ga)Se2 solar cells: A study of alkali doping effects on CIS, CIGS, and CGS using alkali-silicate glass thin layers. *Current Applied Physics*, **2010**, 10, S154-S156	2.6	45
186	Epitaxy of Ge□Sb□Te phase-change memory alloys. *Applied Physics Letters*, **2009**, 94, 041902	3.4	32
185	Flexible Cu(In,Ga)Se2 solar cells fabricated using alkali-silicate glass thin layers as an alkali source material. *Journal of Renewable and Sustainable Energy*, **2009**, 1, 013102	2.5	32
184	Epitaxial Phase Change Materials: Growth and Switching of Ge2Sb2Te5 on GaSb(001). *Materials Research Society Symposia Proceedings*, **2009**, 1160, 1		3
183	Liquid Ge2Sb2Te5 studied by extended x-ray absorption. *Applied Physics Letters*, **2009**, 95, 241902	3.4	24
182	Crystallization of Bi Doped Sb8Te2. *Japanese Journal of Applied Physics*, **2009**, 48, 03A062	1.4	4
181	What is the Origin of Activation Energy in Phase-Change Film?. *Japanese Journal of Applied Physics*, **2009**, 48, 03A053	1.4	39

180	Local structure of amorphous Ge?Sb?Te alloys: Ge umbrella flip vs. DFT simulations. *Physica Status Solidi (B): Basic Research*, **2009**, 246, 1826-1830	1.3	12
179	Large grain Cu(In,Ga)Se2 thin film growth using a Se-radical beam source. *Solar Energy Materials and Solar Cells*, **2009**, 93, 792-796	6.4	21
178	Thermal conductivity of low-k films of varying porosity and direct measurements on silicon substrate. *Microelectronic Engineering*, **2009**, 86, 1009-1012	2.5	5
177	Band profiles of ZnMgO/ZnO heterostructures confirmed by Kelvin probe force microscopy. *Applied Physics Letters*, **2009**, 94, 242107	3.4	29
176	A sensitive multilayered structure suitable for biosensing on the BioDVD platform. *Analytical Chemistry*, **2009**, 81, 4963-70	7.8	37
175	Initial structure memory of pressure-induced changes in the phase-change memory alloy Ge2Sb2Te5. *Physical Review Letters*, **2009**, 103, 115502	7.4	47
174	Na-induced variations in the structural, optical, and electrical properties of Cu(In,Ga)Se2 thin films. *Journal of Applied Physics*, **2009**, 106, 034908	2.5	126
173	Proposal of a grating-based optical reflection switch using phase change materials. *Optics Express*, **2009**, 17, 16947-56	3.3	8
172	Short and Long-Range Order in Phase Change Materials **2009**, 149-174		2
171	Alkali incorporation control in Cu(In,Ga)Se2 thin films using silicate thin layers and applications in enhancing flexible solar cell efficiency. *Applied Physics Letters*, **2008**, 93, 124105	3.4	56
170	Polarization-induced two-dimensional electron gases in ZnMgO/ZnO heterostructures. *Applied Physics Letters*, **2008**, 93, 202104	3.4	105
169	Role of Ge Switch in Phase Transition: Approach using Atomically Controlled GeTe/Sb2Te3Superlattice. *Japanese Journal of Applied Physics*, **2008**, 47, 5763-5766	1.4	62
168	Large Optical Transitions in Rewritable Digital Versatile Discs: An Interlayer Atomic Zipper in a SbTe Alloy. *Materials Research Society Symposia Proceedings*, **2008**, 1072, 1		
167	Changes in electronic structure and chemical bonding upon crystallization of the phase change material GeSb2Te4. *Physical Review Letters*, **2008**, 100, 016402	7.4	48
166	Temperature independence of pressure-induced amorphization of the phase-change memory alloy Ge2Sb2Te5. *Applied Physics Letters*, **2008**, 93, 031918	3.4	32
165	Reduction in crystallization time of Sb:Te films through addition of Bi. *Applied Physics Letters*, **2008**, 92, 141921	3.4	20
164	Thermal conductivity measurements of low-k films using thermoreflectance phenomenon. *Microelectronic Engineering*, **2008**, 85, 796-799	2.5	10
163	Strong excitonic transition of Zn1□MgxO alloy. *Applied Physics Letters*, **2007**, 91, 261907	3.4	52

162	Direct Observation of Nitrogen Location in Molecular Beam Epitaxy Grown Nitrogen-Doped ZnO. *AIP Conference Proceedings*, **2007**,	0	2
161	Phase-change optical recording: Past, present, future. *Thin Solid Films*, **2007**, 515, 7534-7537	2.2	21
160	Measurement of the thermal conductivity of nanometer scale thin films by thermoreflectance phenomenon. *Microelectronic Engineering*, **2007**, 84, 1792-1796	2.5	34
159	Raman scattering study of GeTe and Ge2Sb2Te5 phase-change materials. *Journal of Physics and Chemistry of Solids*, **2007**, 68, 1074-1078	3.9	137
158	High electron mobility Zn polar ZnMgO/ZnO heterostructures grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2007**, 301-302, 358-361	1.6	31
157	Sub-Nanosecond Time-Resolved Structural Measurements of the Phase-Change Alloy Ge2Sb2Te5. *Japanese Journal of Applied Physics*, **2007**, 46, 3711-3714	1.4	12
156	A Reversible Change of Reflected Light Intensity between Molten and Solidified GeSbTe Alloy. *Japanese Journal of Applied Physics*, **2007**, 46, L868-L870	1.4	10
155	Thermal Conductivity Measurements of SbTe Alloy Thin Films Using a Nanosecond Thermoreflectance Measurement System. *Japanese Journal of Applied Physics*, **2007**, 46, 6863-6864	1.4	18
154	Temperature Dependence of the Thermal Properties of Optical Memory Materials. *Japanese Journal of Applied Physics*, **2007**, 46, 3909-3911	1.4	31
153	A possible mechanism of ultrafast amorphization in phase-change memory alloys: an ion slingshot from the crystalline to amorphous position. *Journal of Physics Condensed Matter*, **2007**, 19, 455209	1.8	15
152	Pressure-induced amorphization of quasibinary GeTeSb2Te3: The role of vacancies. *Applied Physics Letters*, **2007**, 91, 021911	3.4	33
151	Existence of tetrahedral site symmetry about Ge atoms in a single-crystal film of Ge2Sb2Te5 found by x-ray fluorescence holography. *Applied Physics Letters*, **2007**, 90, 131913	3.4	30
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